

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC3762

DESCRIPTION

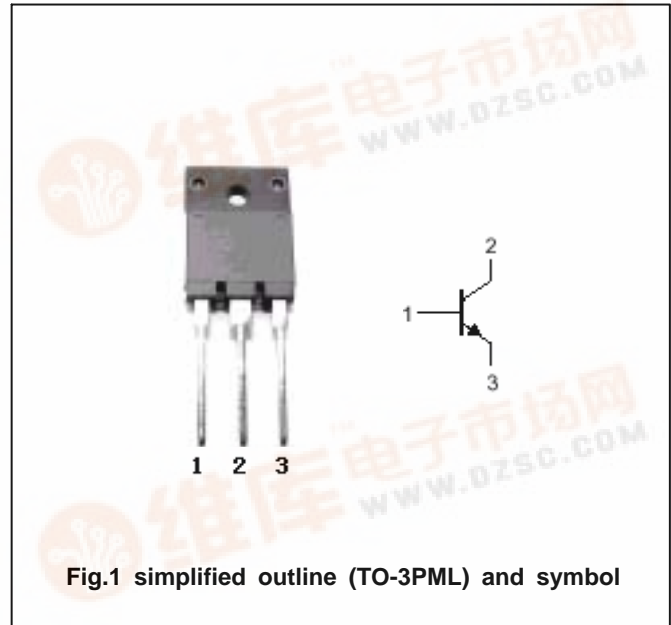
- With TO-3PML package
- High speed switching
- High current capability

APPLICATIONS

- For use in high speed and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		15	A
P _C	Collector dissipation	T _C =25	65	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A ; I _B =1A			0.6	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A ; I _B =1A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =100V ; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =4V ; I _C =0			10	μA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =5V	30		120	

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PACKAGE OUTLINE

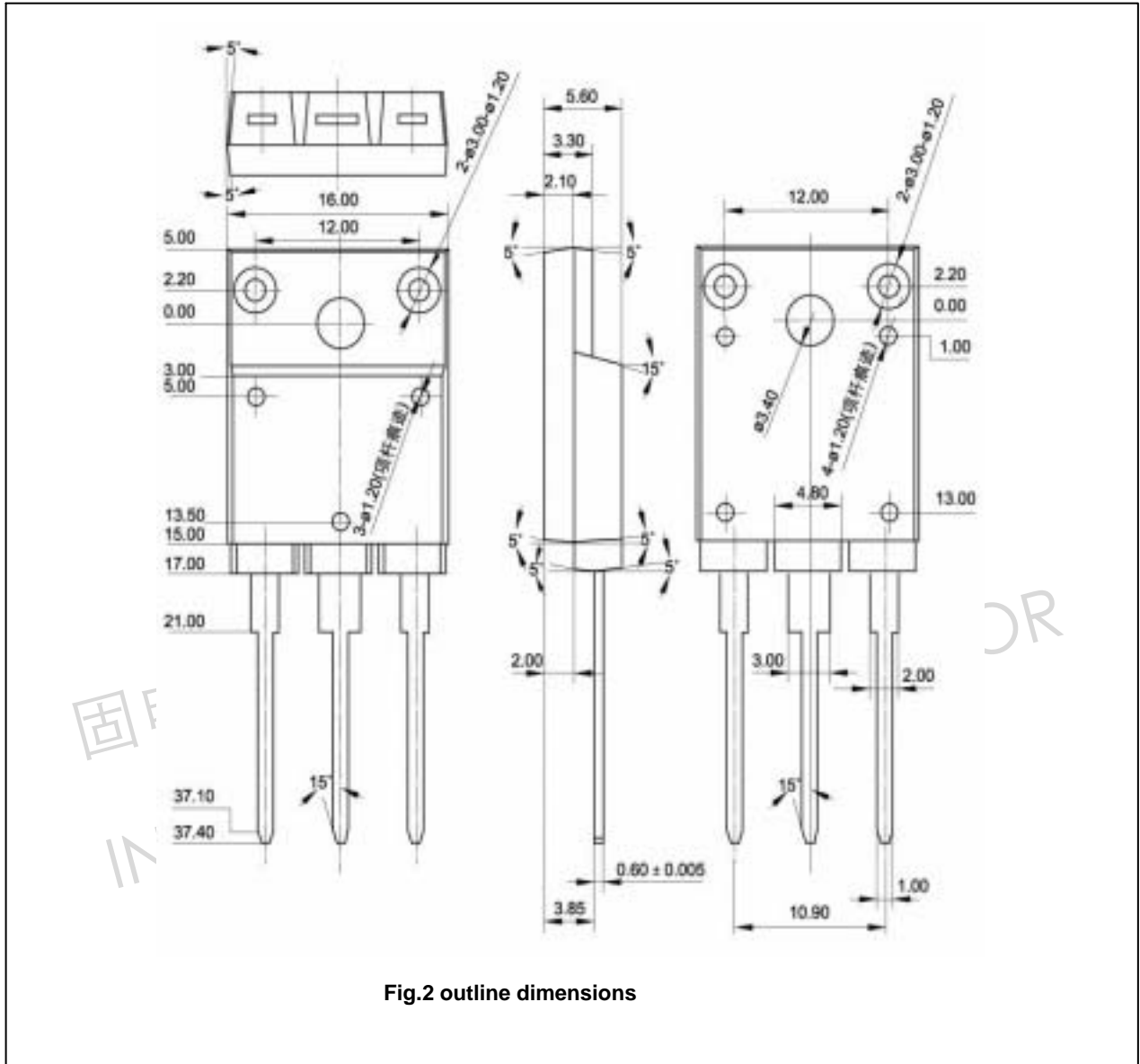


Fig.2 outline dimensions